

	Hits	Search Text	DBs	Time Stamp
1	260	((("257/314-322,390,391").CCLS.) and wells	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/18 09:58
2	27	((mehta-s\$8).in.) and 257/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 10:45
3	196	((("257/314-322,390,391").CCLS.) and wells and @pd<20000711 not dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 11:11
4	195	((("257/314-322,390,391").CCLS.) and wells and @pd<20000711 not dram) and @ad<19990820	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 12:22
5	150	((("257/314-322,390,391").CCLS.) and wells not dram) and @pd<19980820	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 12:23
6	1	03219496.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 13:38
7	3648	("257/314-322,390,391").CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 17:58
8	251	((("257/314-322,390,391").CCLS.) and peripheral and logic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 18:04
9	63	((("257/314-322,390,391").CCLS.) and peripheral with logic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 18:04
10	3364	((("257/314-322,390,391").CCLS.) not dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 18:04
11	211	((("257/314-322,390,391").CCLS.) not dram) and peripheral and logic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:40
12	44	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:40
13	15	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic) and eeprom	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 18:11
14	704	((("257/314-322,390,391").CCLS.) not dram) and insulation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 18:11
15	2449	((("257/314-322,390,391").CCLS.) not dram) and (insulation dielectric oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 18:18
16	524	((("257/314-322,390,391").CCLS.) not dram) and (insulation dielectric oxide) adj layers	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:04
17	169	((("257/314-322,390,391").CCLS.) not dram) and ((insulation nitride dielectric oxide) adj layers) with floating	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:05
18	43	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic and region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:47
19	43	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic and regions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:48
20	39	((("257/314-322,390,391").CCLS.) not dram) and peripheral with logic and regions	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/ 09/17 19:48

	L #	Hits	Search Text	DBs	Time Stam
1	L7	25	(("257/314-322,390,391").CCLS.) and (ONO with oxide) and @pd<19940101	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/18
2	L8	149	(ONO with oxide) and @pd<19940101 not (("257/314-322,390,391").CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/18
3	L9	143	(ONO with oxide) and @pd<19940101 not non-volatile	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/18
4	L10	103	(ONO with oxide) and @pd<19940101 not (non-volatile floating floating-gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/18
5	L11	149	(ONO with oxide) and @pd<19980101 not (non-volatile floating floating-gate CAPACITOR)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2001/09/18

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